





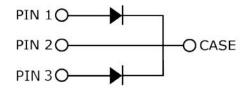
S3D40065D 650V SIC POWER SCHOTTKY RECTIFIER



Description

S3D40065D is a SiC Schottky rectifier packaged in TO-247AD(TO-247-3) case. The device is a high voltage Schottky rectifier that has very low total conduction losses and very stable switching characteristics over temperature extremes. The S3D40065D is ideal for energy sensitive, high frequency applications in challenging environments.

Circuit Diagram



- Alternative energy inverters
- Power Factor Correction (PFC)
- Free-Wheeling diodes

Applications

- · Switching supply output rectification
- Reverse polarity protection

Features

- 175°C T_J operation
- Ultra-low switching loss
- Switching speeds independent of operating temperature
- Low total conduction losses
- High forward surge current capability
- High package isolation voltage
- Terminals finish: 100% Pure Tin
- Pb Free Device
- All SMC parts are traceable to the wafer lot
- Additional electrical and life testing can be performed upon request







Maximum Ratings(per leg)

Characteristics	Symbol	Condition	Max.	Units
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage	V _{RRM} V _{RWM} V _{DC}	-	650	\ \
	I _{F (AV)1}	Tc=25°C	48	А
Average Rectified Forward Current	I _{F (AV)2}	Tc=135°C	21	Α
	I _{F (AV)3}	Tc=140°C	20	Α
	I _{FRM1}	10ms, Half Sine pulse, T _J =25°C	105	Α
Repetitive Peak Forward Surge Current	I _{FRM2}	10ms, Half Sine pulse, T _J =110°C	70	Α
	I _{FSM1}	10ms, Half Sine pulse, T _J =25°C	170	Α
Peak One Cycle Non-Repetitive Surge Current	I _{FSM2}	10ms, Half Sine pulse, Tյ =110°C	145	Α
Non-Repetitive Peak Forward Surge Current	I _{F,Max}	10µs. Pulse, T _J =25°C	1830	Α
Non-Nepetitive Feak Folward Surge Current	I _{F,Max}	10μs. Pulse, Τ _J =110°C	1260	Α
	P _{tot1}	T _J =25°C	136	W
Power Dissipation	P _{tot1}	T _J =110°C	59	W
		M3 Screw	1	Nm
TO-247 Mounting Torque		6-32 Screw	8.8	bf-in

Electrical Characteristics(per leg)

Characteristics	Symbol	Condition	Тур.	Max.	Units
Forward Voltage Drop*	V_{F1}	@ 20A, Pulse, T _J = 25 °C	1.45	1.7	V
Tolward vollage blop	V_{F2}	@ 20A, Pulse, T _J = 175 °C	1.65	2.0	V
Reverse Current*	I _{R1}	$@V_R = \text{rated } V_{R_i} T_J = 25 ^{\circ}\text{C}$	1.5	50	uA
	I _{R2}	$@V_R = \text{rated } V_{R,} T_J = 175 ^{\circ}\text{C}$	15	200	uA
Junction Capacitance	Ст	V _R =0V, T _J =25°C, f=1MHz	1550		pF
Reverse Recovery Charge	Qc	I _F = 20A, di/dt = 200A/μs VR = 400 V, T _J =25°C		ı	nC
Capacitance Stored Energy	Ec	E _C V _R = 400 V		-	μJ

 $^{^*}$ Pulse width < 300 μ s, duty cycle < 2%

Thermal-Mechanical Specifications

Characteristics	Symbol	Condition	Specification	Units
Junction Temperature	TJ	-	-55 to +175	°C
Storage Temperature	T _{stg}	-	-55 to +175	°C
Typical Thermal Resistance Junction to Case	R _θ JC	DC operation	0.84(per leg) 0.42(both leg)	°C/W

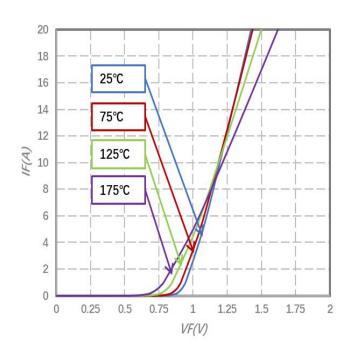
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Ratings and Characteristics Curves (per leg)



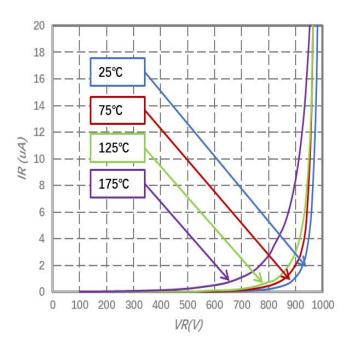
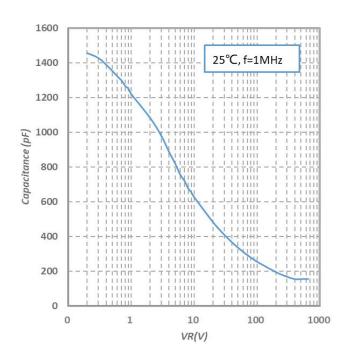


Fig.1-Typical Forward Voltage Characteristics





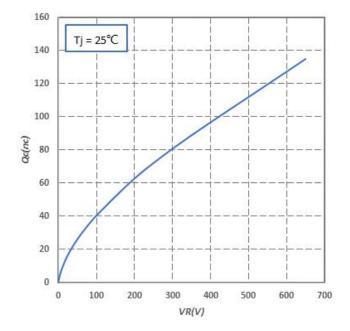


Fig.3-Capacitance vs. Reverse Voltage

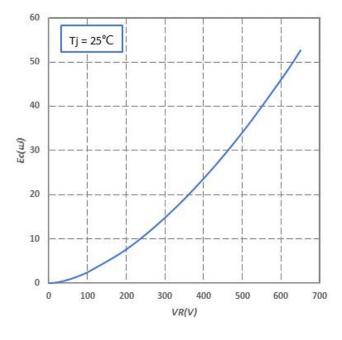
Fig.4-Total Capacitance Charge vs. Reverse Voltage

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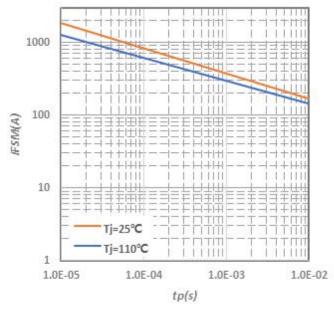
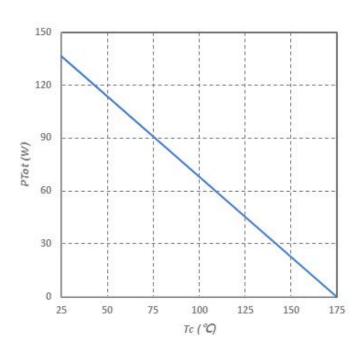


Fig.5-Capacitance Stored Energy

Fig.6-Non-repetitive peak forward surge current versus pulse duration (sinusoidal waveform)



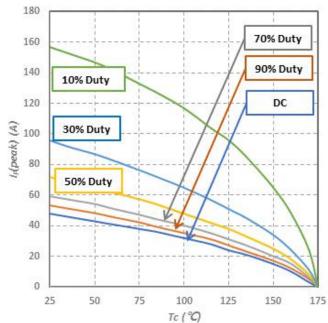


Fig.7-Power Derating

Fig.8-Current Derating

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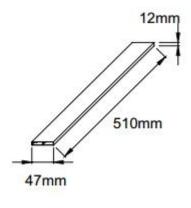


Ordering Information

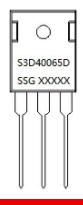
Device	Package	Shipping
S3D40065D	TO-247AD(TO-247-3)	25pcs /tube

For information on tape and reel specifications, including part orientation and tape sizes, please refer to our tape and reel packaging specification.

Tube Specification



Marking Diagram



Where XXXXX is YYWWL

 S3D
 = Device Type

 D
 = Package type

 40
 = Forward Current (40A)

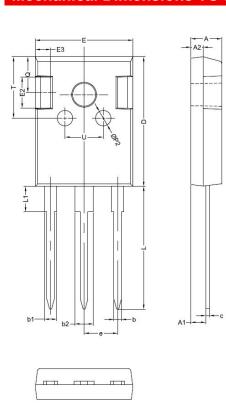
 065
 = Reverse Voltage (650V)

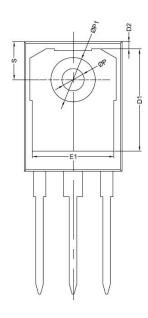
 SSG
 = SSG

YY = Year WW = Week L = Lot Number

Cautions: Molding resin Epoxy resin UL:94V-0

Mechanical Dimensions TO-247AD





CVMDOL	Millimeters			
SYMBOL	MIN.	TYP.	MAX.	
Α	4.80		5.20	
A1	2.00		2.75	
A2	1.90		2.10	
b	1.00		1.40	
b1	1.80		2.40	
b2	2.80		3.40	
С	0.40		0.75	
D	19.80		21.20	
D1		16.55		
D2		1.20		
Е	15.20		16.00	
E1		13.30		
E2		5.00		
E3		2.50		
е	5.20		5.70	
L	13.90		20.70	
L1	3.70		4.30	
Р	3.50		3.70	
P1	7.1		7.40	
P2		2.50		
P2 Q S		5.80		
S	6.05		6.25	
Т		10.00		
U		6.20		

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